



YOUSHANG SEMICONDUCTOR

设计研发新型功率器件

各类小信号开关

中低压及高压大电流等场效应管

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企业微信二维码



企业QQ二维码

Features

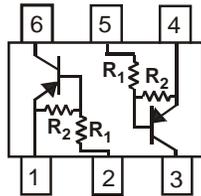
- Epitaxial Planar Die Construction
- Complementary NPN Types Available (DDC)
- Built-In Biasing Resistors

P/N	R1 (NOM)	R2 (NOM)
NK-DDA124EH	22kΩ	22kΩ
NK-DDA144EH	47kΩ	47kΩ
NK-DDA143EH	4.7kΩ	4.7kΩ
NK-DDA114YH	10kΩ	47kΩ
NK-DDA123JH	2.2kΩ	47kΩ
NK-DDA114EH	10kΩ	10kΩ
NK-DDA143TH	4.7kΩ	—
NK-DDA114TH	10kΩ	—

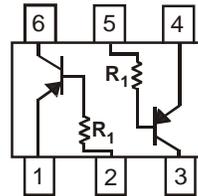
Mechanical Data

- Case: SOT563
- Case Material: Molded Plastic UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish – Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 ^(e)₍₃₎
- Terminal Connections: See Diagram
- Weight: 0.005 grams (Approximate)

SCHEMATIC DIAGRAM, TOP VIEW



R₁, R₂ Device Schematic



R₁ Only Device Schematic

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Supply Voltage		V _{CC}	-50	V
Input Voltage	NK-DDA124EH	V _{IN}	+10 to -40	V
	NK-DDA144EH		+10 to -40	
	NK-DDA143EH		+10 to -30	
	NK-DDA114YH		+6 to -40	
	NK-DDA123JH		+5 to -12	
	NK-DDA114EH		+10 to -40	
	NK-DDA143TH		+5V Max	
	NK-DDA114TH		+5V Max	
Output Current	NK-DDA124EH	I _O	-30	mA
	NK-DDA144EH		-30	
	NK-DDA143EH		-100	
	NK-DDA114YH		-70	
	NK-DDA123JH		-100	
	NK-DDA114EH		-50	
	NK-DDA143TH		-100	
	NK-DDA114TH		-100	
Output Current	All	I _C (Max)	-100	mA
Power Dissipation		P _D	150	mW
Thermal Resistance, Junction to Ambient Air (Note 5)		R _{θJA}	833	°C/W
Operating and Storage Temperature Range		T _J , T _{STG}	-55 to +150	°C

Electrical Characteristics (@ $T_A = +25^\circ\text{C}$ unless otherwise specified.)

Characteristic (DDA143TH & DDA114TH only)	Symbol	Min	Typ	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV_{CBO}	-50	—	—	V	$I_C = -50\mu\text{A}$
Collector-Emitter Breakdown Voltage	BV_{CEO}	-50	—	—	V	$I_C = -1\text{mA}$
Emitter-Base Breakdown Voltage	BV_{EBO}	-5	—	—	V	$I_E = -50\mu\text{A}$
Collector Cut-Off Current	I_{CBO}	—	—	-0.5	μA	$V_{CB} = -50\text{V}$
Emitter Cut-Off Current	I_{EBO}	—	—	-0.5	μA	$V_{EB} = -4\text{V}$
Collector-Emitter Saturation Voltage	$V_{CE(SAT)}$	—	—	-0.3	V	$I_C/I_B = -2.5\text{mA} / -0.25\text{mA}$ DDA143TH $I_C/I_B = -1\text{mA} / -0.1\text{mA}$ DDA114TH
DC Current Transfer Ratio	h_{FE}	100	250	600	—	$I_C = -1\text{mA}$, $V_{CE} = -5\text{V}$
Gain-Bandwidth Product*	f_T	—	250	—	MHz	$V_{CE} = -10\text{V}$, $I_E = 5\text{mA}$, $f = 100\text{MHz}$

Characteristic		Symbol	Min	Typ	Max	Unit	Test Condition
Input Voltage	NK-DDA124EH NK-DDA144EH NK-DDA143EH NK-DDA114YH NK-DDA123JH NK-DDA114EH	$V_{L(OFF)}$	-0.5 -0.5 -0.5 -0.3 -0.5 -0.5	-1.1 -1.1 -1.1 — — -1.1	—	V	$V_{CC} = -5\text{V}$, $I_O = -100\mu\text{A}$
	NK-DDA124EH NK-DDA144EH NK-DDA143EH NK-DDA114YH NK-DDA123JH NK-DDA114EH	$V_{L(ON)}$	—	— — — — -1.9	-1.9 -1.9 -1.9 -1.4 -1.1 -3.0	V	$V_O = -0.3\text{V}$, $I_O = -5\text{mA}$ $V_O = -0.3\text{V}$, $I_O = -2\text{mA}$ $V_O = -0.3\text{V}$, $I_O = -20\text{mA}$ $V_O = -0.3\text{V}$, $I_O = -1\text{mA}$ $V_O = -0.3\text{V}$, $I_O = -5\text{mA}$ $V_O = -0.3\text{V}$, $I_O = -10\text{mA}$
Output Voltage	NK-DDA124EH NK-DDA144EH NK-DDA143EH NK-DDA114YH NK-DDA123JH NK-DDA114EH	$V_{O(ON)}$	—	-0.1	-0.3	V	$I_O/I_L = -10\text{mA} / -0.5\text{mA}$ $I_O/I_L = -10\text{mA} / -0.5\text{mA}$ $I_O/I_L = -10\text{mA} / -0.5\text{mA}$ $I_O/I_L = -5\text{mA} / -0.25\text{mA}$ $I_O/I_L = -5\text{mA} / -0.25\text{mA}$ $I_O/I_L = -10\text{mA} / -0.5\text{mA}$
Input Current	NK-DDA124EH NK-DDA144EH NK-DDA143EH NK-DDA114YH NK-DDA123JH NK-DDA114EH	I_L	—	—	-0.36 -0.18 -1.8 -0.88 -3.6 -0.88	mA	$V_I = -5\text{V}$
Output Current		$I_{O(OFF)}$	—	—	-0.5	μA	$V_{CC} = -50\text{V}$, $V_I = -0\text{V}$
DC Current Gain	NK-DDA124EH NK-DDA144EH NK-DDA143EH NK-DDA114YH NK-DDA123JH NK-DDA114EH	G_L	56 68 20 68 80 30	—	—	—	$V_O = -5\text{V}$, $I_O = -5\text{mA}$ $V_O = -5\text{V}$, $I_O = -5\text{mA}$ $V_O = -5\text{V}$, $I_O = -10\text{mA}$ $V_O = -5\text{V}$, $I_O = -10\text{mA}$ $V_O = -5\text{V}$, $I_O = -10\text{mA}$ $V_O = -5\text{V}$, $I_O = -5\text{mA}$
Gain-Bandwidth Product*		f_T	—	250	—	MHz	$V_{CE} = -10\text{V}$, $I_E = -5\text{mA}$, $f = 100\text{MHz}$

* Transistor - For Reference Only

Typical Curves - DDA143EH

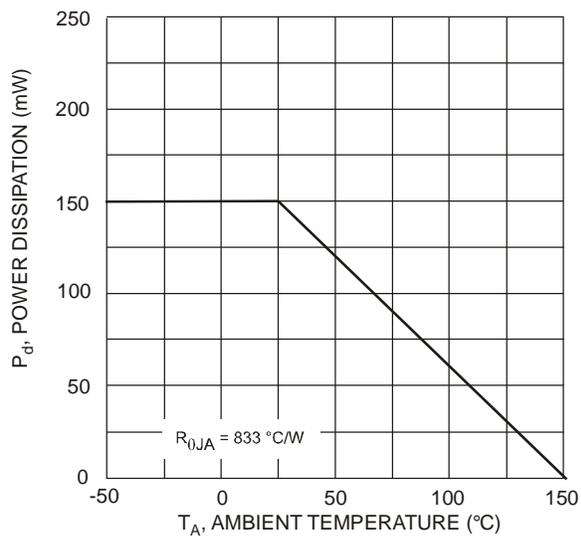


Fig. 1 Derating Curve

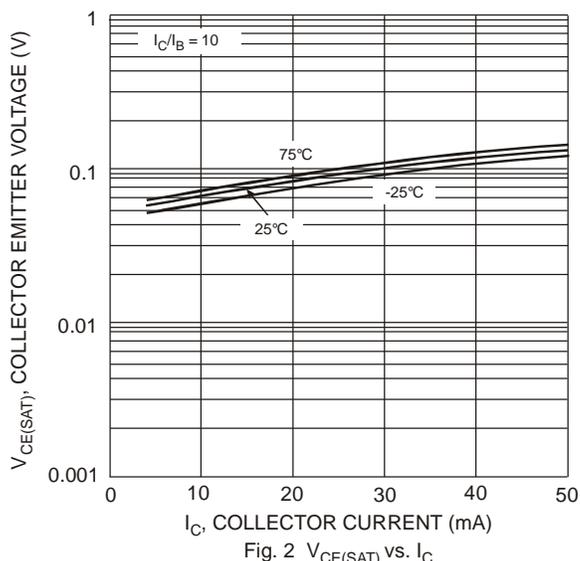


Fig. 2 $V_{CE(SAT)}$ vs. I_C

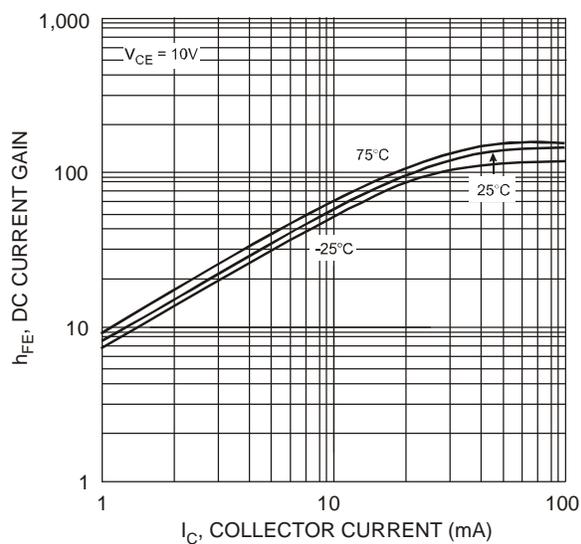


Fig. 3 DC Current Gain

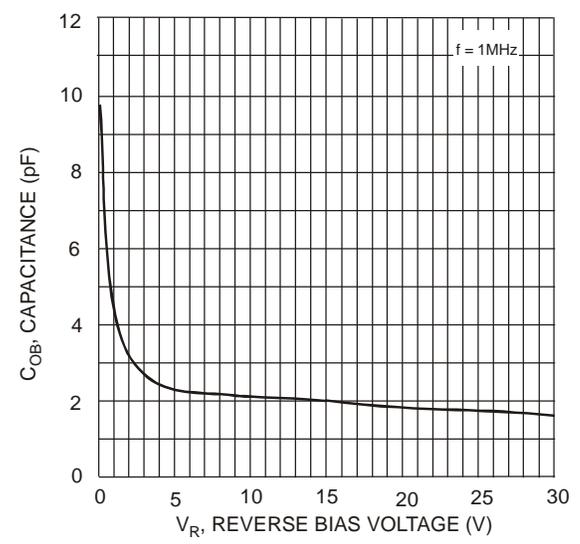


Fig. 4 Output Capacitance

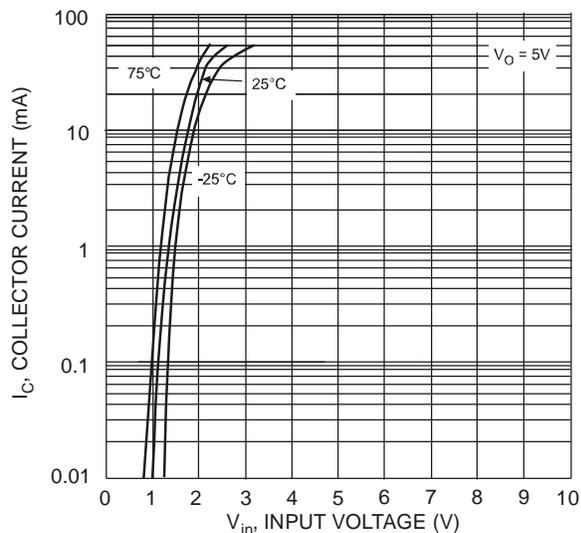


Fig. 5 Collector Current vs. Input Voltage

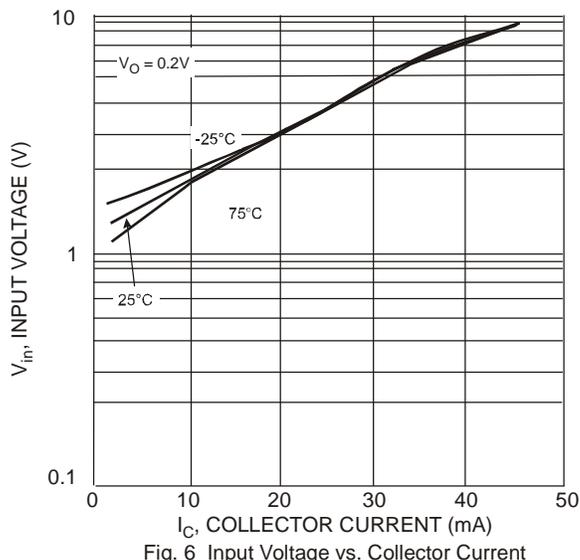
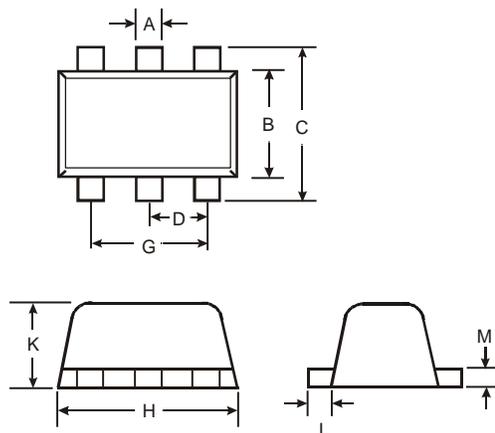


Fig. 6 Input Voltage vs. Collector Current

Package Outline Dimensions

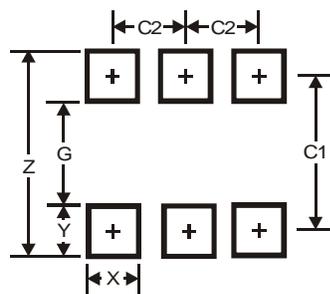
SOT563



SOT563			
Dim	Min	Max	Typ
A	0.15	0.30	0.20
B	1.10	1.25	1.20
C	1.55	1.70	1.60
D	-	-	0.50
G	0.90	1.10	1.00
H	1.50	1.70	1.60
K	0.55	0.60	0.60
L	0.10	0.30	0.20
M	0.10	0.18	0.11
All Dimensions in mm			

Suggested Pad Layout

SOT563



Dimensions	Value (in mm)
Z	2.2
G	1.2
X	0.375
Y	0.5
C1	1.7
C2	0.5